NSN 5962-01-374-7983

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View Online at https://aerobasegroup.com/nsn/5962-01-374-7983

Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

An/tyq-2 (v) 1 e/i fscm 13973

Features Provided:

Electrostatic sensitive and monolithic and programmed and ultraviolet erasable and w/transparent lid

Inclosure Configuration:

Dual-in-line

Output Logic Form:

N-type metal oxide-semiconductor logic

Case Outline Source And Designator:

D-10 mil-m-38510

Current Rating Per Characteristic:

125.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit digital, 262, 144 bit, mos eprom

Voltage Rating And Type Per Characteristic:

-0.6 volts absolute input and 6.25 volts absolute input

Time Rating Per Chacteristic:

200.00 nanoseconds af output megawatts

Memory Device Type:

Eprom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 printed circuit

Specification Data:

81349--38510/22402bya government specification

Purchase Description Identification:

1397-32-475-1313

Departure From Cited Document:

Altered by programming & marking

Shelf Life:

NI/o

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0

